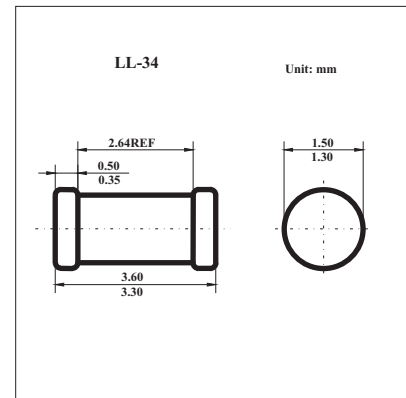


## High Voltage, General Purpose Diode

### KAV103(BAV103)

#### ■ Features

- Silicon Epitaxial Planar Diodes
- For general purpose



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Working Inverse Voltage	$W_{iv}$	200	V
Average Rectified Current	$I_o$	200	mA
DC Forward Current	$I_F$	500	mA
Recurrent Peak Forward Current	$i_f$	600	mA
Peak Forward Surge Current	$i_{F(surge)}$	1	A
		4	
Total Power Dissipation at $T_A = 25^\circ\text{C}$	$P_D$	500	mW
Linear Derating Factor from $T_A = 25^\circ\text{C}$		3.33	mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$
Operating Junction Temperature	$T_J$	-65 to +200	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +200	$^\circ\text{C}$

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Breakdown Voltage	$B_V$	$I_R = 100 \mu\text{A}$	250			V
Reverse Leakage	$I_R$	$V_R = 200 \text{ V}$			100	nA
		$V_R = 200 \text{ V } T_A = 150^\circ\text{C}$			100	$\mu\text{A}$
Forward Voltage	$V_F$	$I_F = 100 \text{ mA}$			1.00	V
		$I_F = 200 \text{ mA}$			1.25	V
Capacitance	$C_T$	$V_R = 0.0 \text{ V}, f = 1.0 \text{ MHz}$			5.0	pF
Reverse Recovery Time	$T_{RR}$	$I_F = I_R = 30 \text{ mA}, I_{RR} = 1.0 \text{ mA}, R_L = 100 \Omega$			50	ns